



ATTORNEY'S DOCKET NO.: 07977/088002/US3155D1

GAU 28128

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Hongyong Zhang
Serial No.: 09/362,808
Filed : July 28, 1999
Title : METHOD OF FABRICATING SEMICONDUCTOR DEVICE

Art Unit : 2812
Examiner :

Assistant Commissioner for Patents
Washington, D.C. 20231

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TRANSMITTAL LETTER

TECHNOLOGY CENTER 2800

Correspondence relating to this application is enclosed.
The required fees are computed below. Please apply any charges
not covered, or any credits, to Deposit Account No. 06-1050.

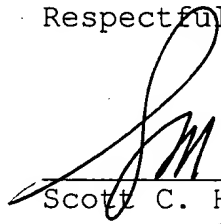
Total Claims	30	-	20	=	10	\$180
Independent	6	-	3	=	3	\$234

TOTAL FEE DUE \$414

A check for \$414 is attached.

Respectfully submitted,

Date: 3/6/00



Scott C. Harris
Reg. No. 32,030

SCH/smr
PTO Customer No. 20985
Fish & Richardson P.C.
4350 La Jolla Village Drive, Suite 500
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for Patents, Washington, D.C. 20231.

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Susan Regan
Signature

SUSAN REGAN
Typed or Printed Name of Person Signing Certificate



Attorney's Document No.: 07977/088002/US3155

21/B Pre
Amend
328W
O. Cant

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : H. Zhang Art Unit : 2812
Serial No. : 09/362,808 Examiner : Unknown
Filed : July 28, 1999
Title : METHOD OF FABRICATING SEMICONDUCTOR DEVICE

Assistant Commissioner for Patents
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SUPPLEMENTAL PRELIMINARY AMENDMENT

TECHNOLOGY CENTER 2800

Sir:

Prior to initial examination and supplemental to the Preliminary Amendment filed January 18, 2000, kindly amend the above-identified application as follows.

In the Claims:

Please amend the following claim.

6. (Amended) A semiconductor device comprising:
a semiconductor layer formed over a substrate having an insulating surface, said semiconductor layer having at least channel, source and drain regions;
a gate insulating film over [a] said semiconductor layer;

B1
sub
C2

CERTIFICATE OF MAILING BY FIRST CLASS MAIL

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Susan Regan

Signature

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01 FC:103
02 FC:102

180.00 DP
234.00 DP